

ZHCSA64 - AUGUST 2012 www.ti.com.cn

双路双输入正或门

查询样品: SN74LVC2G32-Q1

特性

- 符合汽车应用要求
- 具有符合 AEC-Q100 的下列结果:
 - 器件温度 1 级: -40°C 至 125°C 的环境运行温 度范围
 - 器件人体模型 (HBM) 静电放电 (ESD) 分类等级
 - 器件充电器件模型 (CDM) ESD 分类等级 C3B
- 输入接受的电压达到 5.5V
- 3.3V 时, 最大传播(延迟)时间为 3.8ns
- 低功耗,最大电源电流 10µA
- 3.3V 时,输出驱动 ±24mA

- 在V_{CC}=3.3 V, T_A=25°C 时, 典型电压输出低峰 值(输出地弹反射)
- 在 V_{CC}=3.3V, T_A=25°C 时, 典型电压输出高谷值 (V_{OH}下冲) >2V
- **Ⅰ**_{★闭}状态电流支持部分断电模式运行

应用范围

- 车载应用
- 逻辑和栅极

DCU PACKAGE (TOP VIEW) 1A □ 1B ∏ 6 □ 2B 2Y 🗆 3 5 GND Ⅲ □ 2A

说明

这个双路上输入正或门被设计用于 1.65V 至 5.5V 集流器电源电压运行。

SN74LVC2G32-Q1 在正逻辑中Y = A + B or Y = $\overline{A \bullet B}$ 执行布尔函数。

NanoFree™ 封装技术是IC 封装概念的一项重大突破,它将硅晶片用作封装。

该器件完全符合使用关闭状态电流的部分断电应用的规范要求。 关闭状态电流电路禁用输出,从而可防止其断电时 破坏性电流从该器件回流。

ORDERING INFORMATION(1)

T _A	PACK	AGE ⁽²⁾	ORDERABLE PART NUMBER	TOP-SIDE MARKING	
-40°C to 125°C	VSSOP - DCU	Reel of 3000	SN74LVC2G32QDCURQ1	SUCQ	

For the most current package and ordering information, see the Package Option Addendum at the end of this document, or see the TI web site at www.ti.com.

Package drawings, thermal data, and symbolization are available at www.ti.com/packaging.

Please be aware that an important notice concerning availability, standard warranty, and use in critical applications of Texas Instruments semiconductor products and disclaimers thereto appears at the end of this data sheet. NanoFree is a trademark of Texas Instruments.

ZHCSA64 - AUGUST 2012

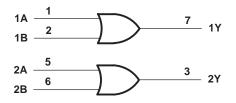


These devices have limited built-in ESD protection. The leads should be shorted together or the device placed in conductive foam during storage or handling to prevent electrostatic damage to the MOS gates.

FUNCTION TABLE (EACH GATE)

INP	OUTPUT			
Α	В	Y		
Н	Χ	Н		
X	Н	Н		
L	L	L		

LOGIC DIAGRAM (POSITIVE LOGIC)



ABSOLUTE MAXIMUM RATINGS(1)

over operating free-air temperature range (unless otherwise noted)

			MIN	MAX	UNIT
V_{CC}	Supply voltage range		-0.5	6.5	V
VI	Input voltage range (2)		-0.5	6.5	V
Vo	Voltage range applied to	-0.5	6.5	V	
Vo	Voltage range applied to	-0.5	$V_{CC} + 0.5$	V	
I_{IK}	Input clamp current		- 50	mΑ	
I _{OK}	Output clamp current	V _O < 0		- 50	mΑ
Io	Continuous output currer	nt		±50	mΑ
	Continuous current throu	igh V _{CC} or GND		±100	mΑ
T _{stg}	Storage temperature ran	ge	-65	150	°C
	ESD Boting	Human body model (HBM) AEC-Q100 classification level H2		2	kV
	ESD Rating	Charged device model (CDM) AEC-Q100 classification level C3B		750	V

Stresses beyond those listed under Absolute Maximum Ratings may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated under Recommended Operating Conditions is not implied. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.

THERMAL INFORMATION

	THERMAL METRIC ⁽¹⁾	SN74LVC2G32-Q1	LINUT	
	THERMAL METRIC	DCU (8 PINS)	UNIT	
θ_{JA}	Junction-to-ambient thermal resistance	204.4		
θ_{JCtop}	Junction-to-case (top) thermal resistance	77		
θ_{JB}	Junction-to-board thermal resistance	83.2	°C/W	
ΨЈТ	Junction-to-top characterization parameter	7.1	C/VV	
ΨЈВ	Junction-to-board characterization parameter	82.7		
θ_{JCbot}	Junction-to-case (bottom) thermal resistance	N/A		

RUMENTS

www.ti.com.cn

The input negative-voltage and output voltage ratings may be exceeded if the input and output clamp-current ratings are observed.

⁽³⁾ The value of V_{CC} is provided in the recommended operating conditions table.



www.ti.com.cn ZHCSA64 – AUGUST 2012

RECOMMENDED OPERATING CONDITIONS(1)

			MIN	MAX	UNIT
.,	Ownerhouselfanse	Operating	1.65	5.5	
V_{CC}	Supply voltage	Data retention only	1.5		V
		V _{CC} = 1.65 V to 1.95 V	0.65 × V _{CC}		
.,	I Pale Java Parasta antique	V _{CC} = 2.3 V to 2.7 V	1.7		.,
V_{IH}	High-level input voltage	V _{CC} = 3 V to 3.6 V	2		V
		V _{CC} = 4.5 V to 5.5 V	0.7 × V _{CC}		
		V _{CC} = 1.65 V to 1.95 V		0.35 × V _{CC}	
.,	Law law Line to the ma	V _{CC} = 2.3 V to 2.7 V		0.7	V
V_{IL}	Low-level input voltage	V _{CC} = 3 V to 3.6 V		0.8	V
		V _{CC} = 4.5 V to 5.5 V			
VI	Input voltage	·	0	5.5	V
Vo	Output voltage		0	V _{CC}	V
		V _{CC} = 1.65 V		-4	
		V _{CC} = 2.3 V		-8	
I_{OH}	High-level output current	V 0V		-16	mA
		$V_{CC} = 3 V$		-24	
		V _{CC} = 4.5 V		-32	
		V _{CC} = 1.65 V		4	
		V _{CC} = 2.3 V		8	
I_{OL}	Low-level output current	V 0V		16	mA
		$V_{CC} = 3 V$		24	
		V _{CC} = 4.5 V		32	
		$V_{CC} = 1.8 \text{ V} \pm 0.15 \text{ V}, 2.5 \text{ V} \pm 0.2 \text{ V}$		20	
Δt/Δν	Input transition rise or fall rate	$V_{CC} = 3.3 \text{ V} \pm 0.3 \text{ V}$	10		ns/V
		$V_{CC} = 5 \text{ V} \pm 0.5 \text{ V}$			
T _A	Operating free-air temperature		-40	125	°C

⁽¹⁾ All unused inputs of the device must be held at V_{CC} or GND to ensure proper device operation. Refer to the TI application report, Implications of Slow or Floating CMOS Inputs, literature number SCBA004.

TEXAS INSTRUMENTS

ZHCSA64 – AUGUST 2012 www.ti.com.cn

ELECTRICAL CHARACTERISTICS

over recommended operating free-air temperature range (unless otherwise noted)

PARAMETER	TEST CONDITIONS	V _{cc}	MIN TYP ⁽¹⁾ MAX	UNIT	
V _{OH}	$I_{OH} = -100 \mu A$	1.65 V to 5.5 V	V _{CC} - 0.1		
	$I_{OH} = -4 \text{ mA}$	1.65 V	1.2		
	$I_{OH} = -8 \text{ mA}$	2.3 V	1.9	V	
	$I_{OH} = -16 \text{ mA}$	3 V	2.4	V	
	$I_{OH} = -24 \text{ mA}$	3 V	2.3		
	$I_{OH} = -32 \text{ mA}$	4.5 V	3.8		
	I _{OL} = 100 μA	1.65 V to 5.5 V	0.1		
	I _{OL} = 4 mA	1.65 V	0.45		
V _{OL}	I _{OL} = 8 mA	2.3 V	0.3	V	
	I _{OL} = 16 mA	2.1/	0.4	V	
	I _{OL} = 24 mA	3 V	0.6		
	I _{OL} = 32 mA	4.5 V	0.6		
I _I A or B inputs	V _I = 5.5 V or GND	0 to 5.5 V	±5	μΑ	
I _{off}	V_I or $V_O = 5.5 \text{ V}$	0	±10	μA	
I _{cc}	$V_I = 5.5 \text{ V or GND}, \qquad I_O = 0$	1.65 V to 5.5 V	10	μA	
ΔI _{CC}	One input at V_{CC} – 0.6 V, Other inputs at V_{CC} or GND	3 V to 5.5 V	500	μΑ	
C _i	$V_I = V_{CC}$ or GND	3.3 V	5	pF	

⁽¹⁾ All typical values are at V_{CC} = 3.3 V, T_A = 25°C.

SWITCHING CHARACTERISTICS

over recommended operating free-air temperature range (unless otherwise noted) (see Figure 1)

PARAMETER	FROM (INPUT)	TO (OUTPUT)	V _{CC} = ± 0.1		V _{CC} = 1 ± 0.2		V _{CC} = ± 0.3		V _{CC} = 5 V ± 0.5 V		UNIT
	(INPUT)	(001701)	MIN	MAX	MIN	MAX	MIN	MAX	MIN	MAX	
t _{pd}	A or B	Υ	2.4	11	1	7.5	1	5.8	1	4.7	ns

OPERATING CHARACTERISTICS

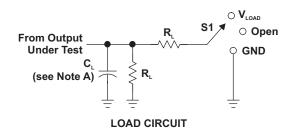
 $T_A = 25$ °C

PARAMETER		TEST CONDITIONS	V _{CC} = 1.8 V TYP	V _{CC} = 2.5 V TYP	V _{CC} = 3.3 V TYP	V _{CC} = 5 V TYP	UNIT
C_{pd}	Power dissipation capacitance	f = 10 MHz	17	17	17	19	pF



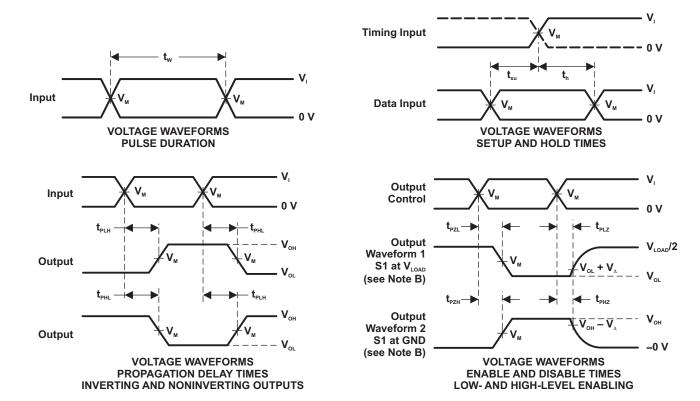
www.ti.com.cn ZHCSA64 – AUGUST 2012

PARAMETER MEASUREMENT INFORMATION



TEST	S1
t _{PLH} /t _{PHL}	Open
$t_{_{\mathrm{PLZ}}}/t_{_{\mathrm{PZL}}}$	V _{LOAD}
t _{PHZ} /t _{PZH}	GND

V _{cc}	INI	PUTS	.,,	v		-	.,
	V,	t,/t,	V _M	V _{LOAD}	C _∟	$R_{\scriptscriptstyle L}$	V _A
1.8 V ± 0.15 V	V _{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	1 k Ω	0.15 V
2.5 V ± 0.2 V	V_{cc}	≤2 ns	V _{cc} /2	2 × V _{cc}	30 pF	500 Ω	0.15 V
3.3 V ± 0.3 V	3 V	≤2.5 ns	1.5 V	6 V	50 pF	500 Ω	0.3 V
5 V ± 0.5 V	V_{cc}	≤2.5 ns	V _{cc} /2	2 × V _{cc}	50 pF	500 Ω	0.3 V



NOTES: A. C_L includes probe and jig capacitance.

- B. Waveform 1 is for an output with internal conditions such that the output is low, except when disabled by the output control. Waveform 2 is for an output with internal conditions such that the output is high, except when disabled by the output control.
- C. All input pulses are supplied by generators having the following characteristics: PRR \leq 10 MHz, Z_{o} = 50 Ω .
- D. The outputs are measured one at a time, with one transition per measurement.
- E. $t_{\mbox{\tiny PLZ}}$ and $\dot{t}_{\mbox{\tiny PHZ}}$ are the same as $t_{\mbox{\tiny dis}}.$
- F. $t_{\mbox{\tiny PZL}}$ and $t_{\mbox{\tiny PZH}}$ are the same as $t_{\mbox{\tiny en}}.$
- G. t_{PLH} and t_{PHL} are the same as t_{pd} .
- H. All parameters and waveforms are not applicable to all devices.

Figure 1. Load Circuit and Voltage Waveforms





10-Dec-2020

PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan	Lead finish/ Ball material	MSL Peak Temp	Op Temp (°C)	Device Marking (4/5)	Samples
SN74LVC2G32DCTR	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C32 (R, Z)	Samples
SN74LVC2G32DCTRE4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C32 (R, Z)	Samples
SN74LVC2G32DCTRG4	ACTIVE	SM8	DCT	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C32 (R, Z)	Samples
SN74LVC2G32DCUR	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C32J, C32Q, C32R) CR	Samples
SN74LVC2G32DCURE4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C32R	Samples
SN74LVC2G32DCURG4	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	C32R	Samples
SN74LVC2G32DCUT	ACTIVE	VSSOP	DCU	8	250	RoHS & Green	NIPDAU SN	Level-1-260C-UNLIM	-40 to 125	(C32J, C32Q, C32R) CR	Samples
SN74LVC2G32QDCURQ1	ACTIVE	VSSOP	DCU	8	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	SUCQ	Samples
SN74LVC2G32YZPR	ACTIVE	DSBGA	YZP	8	3000	RoHS & Green	SNAGCU	Level-1-260C-UNLIM	-40 to 85	CGN	Samples

(1) The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

PREVIEW: Device has been announced but is not in production. Samples may or may not be available.

OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.



PACKAGE OPTION ADDENDUM

10-Dec-2020

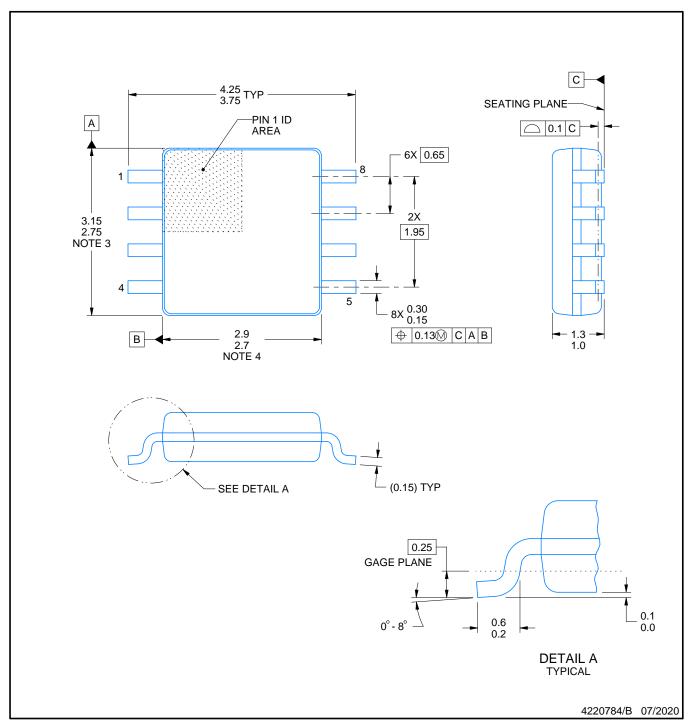
- (4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.
- (5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.
- (6) Lead finish/Ball material Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

Important Information and Disclaimer: The information provided on this page represents TI's knowledge and belief as of the date that it is provided. TI bases its knowledge and belief on information provided by third parties, and makes no representation or warranty as to the accuracy of such information. Efforts are underway to better integrate information from third parties. TI has taken and continues to take reasonable steps to provide representative and accurate information but may not have conducted destructive testing or chemical analysis on incoming materials and chemicals. TI and TI suppliers consider certain information to be proprietary, and thus CAS numbers and other limited information may not be available for release.

In no event shall TI's liability arising out of such information exceed the total purchase price of the TI part(s) at issue in this document sold by TI to Customer on an annual basis.



SMALL OUTLINE PACKAGE



NOTES:

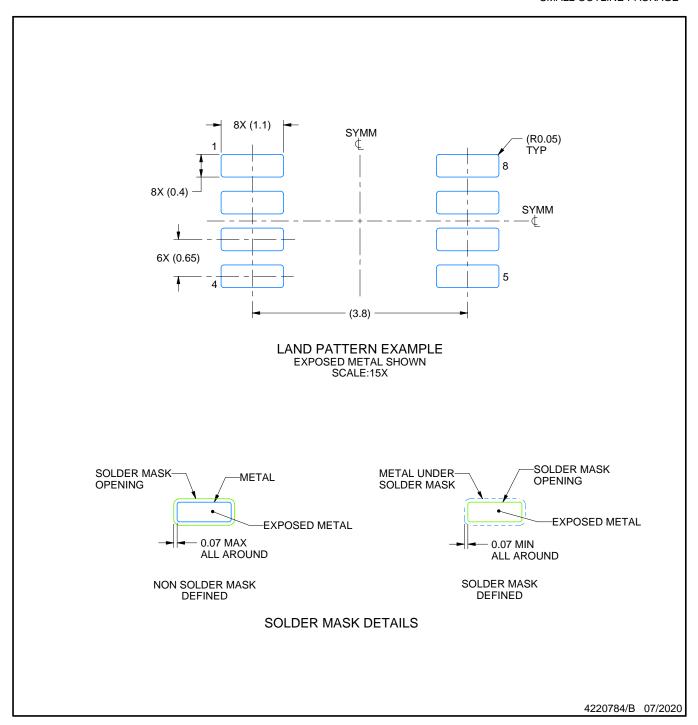
- 1. All linear dimensions are in millimeters. Dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.

 3. This dimension does not include mold flash, protrusions, or gate burrs. Mold flash, protrusions, or gate burrs shall not
- exceed 0.15 mm per side.
- 4. This dimension does not include interlead flash. Interlead flash shall not exceed 0.25 mm per side.
- 5. Reference JEDEC registration MS-187.



SMALL OUTLINE PACKAGE

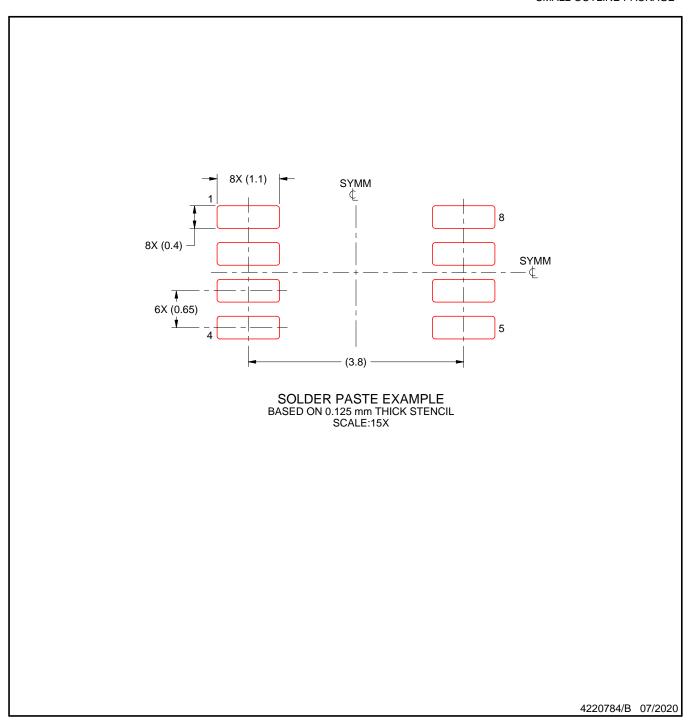


NOTES: (continued)

6. Publication IPC-7351 may have alternate designs.7. Solder mask tolerances between and around signal pads can vary based on board fabrication site.



SMALL OUTLINE PACKAGE



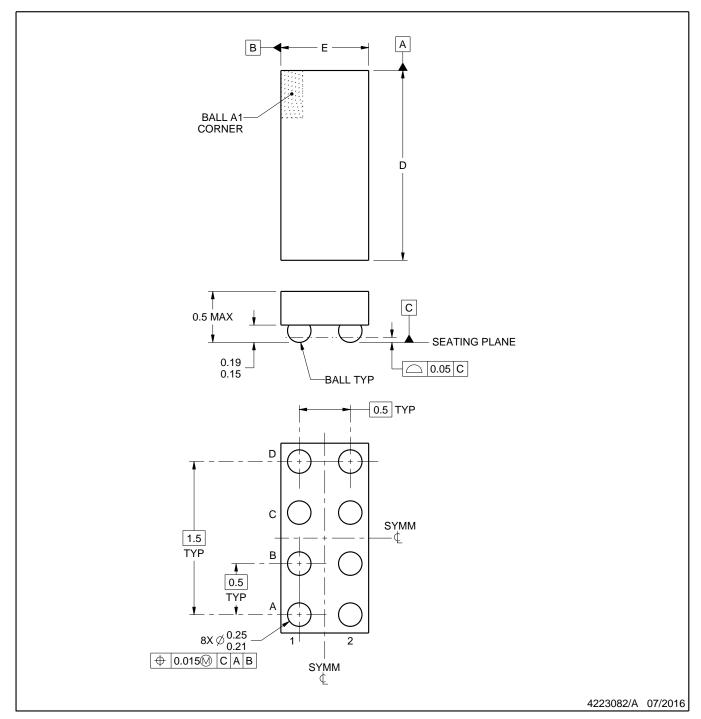
NOTES: (continued)

- 8. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.
- 9. Board assembly site may have different recommendations for stencil design.





DIE SIZE BALL GRID ARRAY



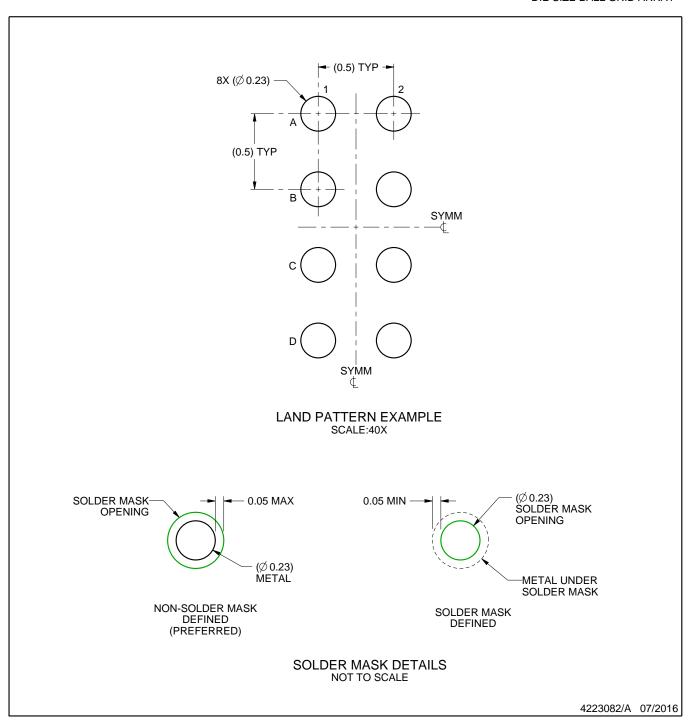
NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.

 2. This drawing is subject to change without notice.



DIE SIZE BALL GRID ARRAY

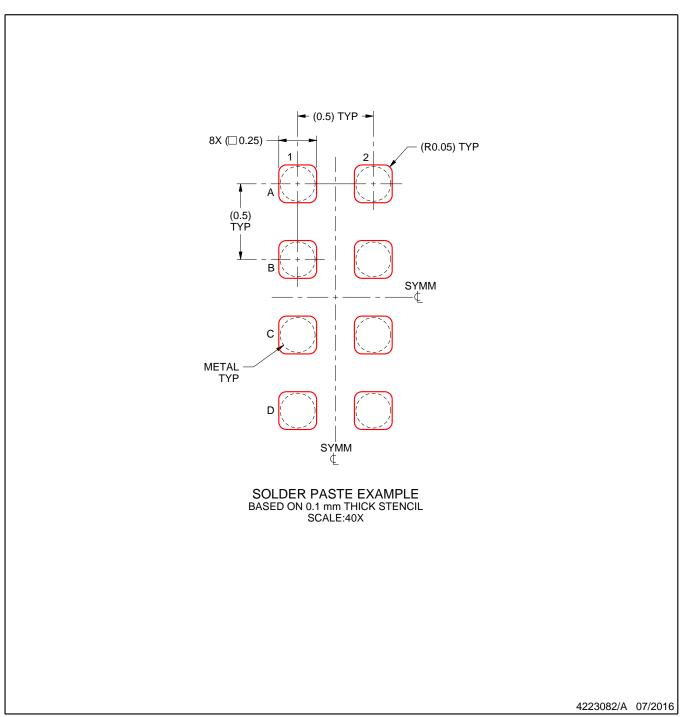


NOTES: (continued)

3. Final dimensions may vary due to manufacturing tolerance considerations and also routing constraints. For more information, see Texas Instruments literature number SNVA009 (www.ti.com/lit/snva009).



DIE SIZE BALL GRID ARRAY



NOTES: (continued)

4. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release.



DCU (R-PDSO-G8)

PLASTIC SMALL-OUTLINE PACKAGE (DIE DOWN)



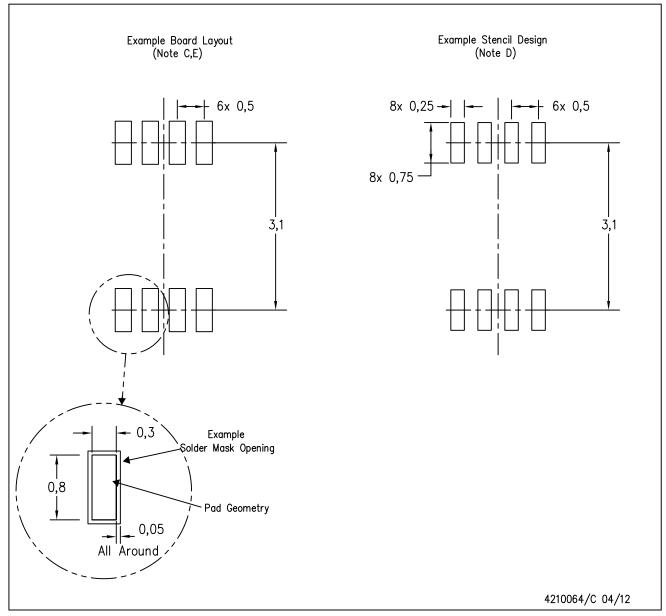
NOTES:

- : A. All linear dimensions are in millimeters.
 - B. This drawing is subject to change without notice.
 - C. Body dimensions do not include mold flash or protrusion. Mold flash and protrusion shall not exceed 0.15 per side.
 - D. Falls within JEDEC MO-187 variation CA.



DCU (S-PDSO-G8)

PLASTIC SMALL OUTLINE PACKAGE (DIE DOWN)



NOTES: A. All linear dimensions are in millimeters.

- B. This drawing is subject to change without notice.
- C. Publication IPC-7351 is recommended for alternate designs.
- D. Laser cutting apertures with trapezoidal walls and also rounding corners will offer better paste release. Customers should contact their board assembly site for stencil design recommendations. Refer to IPC-7525 for other stencil recommendations.
- E. Customers should contact their board fabrication site for solder mask tolerances between and around signal pads.



重要声明和免责声明

TI 均以"原样"提供技术性及可靠性数据(包括数据表)、设计资源(包括参考设计)、应用或其他设计建议、网络工具、安全信息和其他资源,不保证其中不含任何瑕疵,且不做任何明示或暗示的担保,包括但不限于对适销性、适合某特定用途或不侵犯任何第三方知识产权的暗示担保。

所述资源可供专业开发人员应用TI产品进行设计使用。您将对以下行为独自承担全部责任: (1)针对您的应用选择合适的TI产品; (2)设计、验证并测试您的应用; (3)确保您的应用满足相应标准以及任何其他安全、安保或其他要求。所述资源如有变更,恕不另行通知。TI对您使用所述资源的授权仅限于开发资源所涉及TI产品的相关应用。除此之外不得复制或展示所述资源,也不提供其它TI或任何第三方的知识产权授权许可。如因使用所述资源而产生任何索赔、赔偿、成本、损失及债务等,TI对此概不负责,并且您须赔偿由此对TI及其代表造成的损害。

TI 所提供产品均受TI 的销售条款 (http://www.ti.com.cn/zh-cn/legal/termsofsale.html) 以及ti.com.cn上或随附TI产品提供的其他可适用条款的约束。TI提供所述资源并不扩展或以其他方式更改TI 针对TI 产品所发布的可适用的担保范围或担保免责声明。

邮寄地址: 上海市浦东新区世纪大道 1568 号中建大厦 32 楼,邮政编码: 200122 Copyright © 2020 德州仪器半导体技术(上海)有限公司